Supporting Information for

Highly Efficient and Stable FAPbI₃ Perovskite Solar Cells and Modules Based on Exposure of the (011) Facet

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Supplementary Figures



Fig. S1 Schematic showing the change in the stacking of (001) and (011) planes induced by [4MBP]Cl



Fig. S2 Scanning electron microscopy (SEM) images and grain size distribution of perovskite films **a-b**) without and **c-d**) with 0.5 mol% [4MBP]Cl



Fig. S3 Time-of-flight secondary ion mass spectrometry depth profiles for perovskite solar cells (PSCs) **a**) without and **b**) with 0.5 mol% [4MBP]Cl



Fig. S4 SEM images of perovskite films with 4.0 mol% [4MBP]Cl under different magnifications, a) 50000X and b) 10000X



Fig. S5 a) J_{sc} , b) V_{oc} , c) PCE and d) FF of the control and [4MBP]Cl-doped devices



Fig. S6 IPCE of devices fabricated without and with 0.5 mol% [4MBP]Cl



Fig. S7 J-V curves of devices fabricated without and with 0.5 mol% [4MBP]Cl



Fig. S8 a) UV-vis absorption spectra of perovskite films without and with 0.5 mol% [4MBP]Cl. **b)** Tauc plot of the corresponding UV-vis plot of the perovskite films without and with 0.5 mol% [4MBP]Cl



Fig. S9 UPS of perovskite films without and with 0.5 mol% [4MBP]Cl

The Fermi energy level (E_F) and valence band maximum (VBM) can be obtained using the following equations: $E_F = E_{cut-off}$ -21.22 (1) and VBM = $-E_F + E_{onset}$ (2). $E_{cut-off}$ and E_{onset} are 17.39 and 1.86 eV, respectively, for the control film. Similarly, $E_{cut-off}$ and E_{onset} of the [4MBP]Cl-modified film are 17.22 and 1.90 eV, respectively. The VBM of control and the [4MBP]Cl-doped films were calculated as -5.69 and -5.90 eV, respectively. Based on the optical energy band gap, the conduction band minimum (CBM) values for the control and [4MBP]Cl-modified film are -4.12 and -4.33 eV, respectively.



Fig. S10 KPFM images of perovskite films a) without and b) with 0.5 mol% [4MBP]Cl



Fig. S11 a) PL spectra and **b)** TRPL spectra of perovskite films without and with 0.5 mol% [4MBP]Cl deposited on FTO substrates



Fig. S12 SCLC curves of devices a) without and b) with 0.5 mol% [4MBP]Cl



Fig. S13 V_{oc} dependence on the light intensity for the PSCs without and with 0.5 mol% [4MBP]Cl



Fig. S14 a) J_{sc} , b) V_{oc} and c) FF of modules without and with 0.5 mol% [4MBP]C1



Fig. S15 a) PCE evolution of the unencapsulated PSCs without and with 0.5 mol% [4MBP]Cl at 60 °C under N₂ in the dark. b) XRD evolution of perovskite degradation without and with 0.5 mol% [4MBP]Cl at 60 °C under N₂ in the dark